

# XN01504 (XN1504)

## Silicon NPN epitaxial planer transistor

For amplification of low frequency output

### Features

- Two elements incorporated into one package.  
(Emitter-coupled transistors)
- Reduction of the mounting area and assembly cost by one half.

### Basic Part Number of Element

- 2SD1915F × 2 elements

### Absolute Maximum Ratings (Ta=25°C)

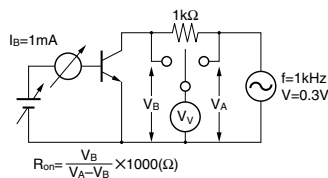
|                   | Parameter                    | Symbol    | Ratings     | Unit |
|-------------------|------------------------------|-----------|-------------|------|
| Rating of element | Collector to base voltage    | $V_{CBO}$ | 50          | V    |
|                   | Collector to emitter voltage | $V_{CEO}$ | 20          | V    |
|                   | Emitter to base voltage      | $V_{EBO}$ | 25          | V    |
|                   | Collector current            | $I_C$     | 300         | mA   |
|                   | Peak collector current       | $I_{CP}$  | 500         | mA   |
| Overall           | Total power dissipation      | $P_T$     | 300         | mW   |
|                   | Junction temperature         | $T_j$     | 150         | °C   |
|                   | Storage temperature          | $T_{stg}$ | -55 to +150 | °C   |

### Electrical Characteristics (Ta=25°C)

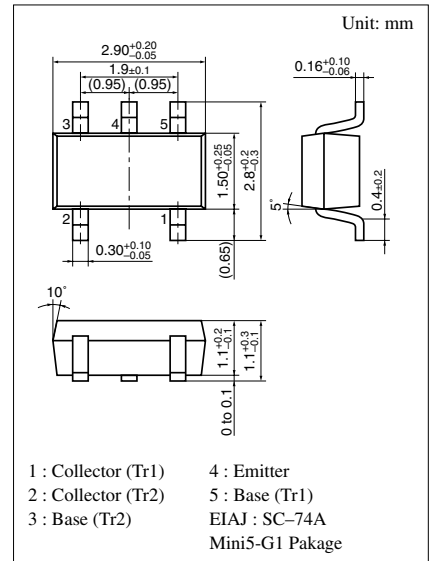
| Parameter                               | Symbol                            | Conditions   | min | typ  | max  | Unit          |
|---|-----------------------------------|--|-----|------|------|---------------|
| Collector to emitter voltage            | $V_{CEO}$                         | $I_C = 1\text{mA}, I_B = 0$                                | 20  |      |      | V             |
| Collector cutoff current                | $I_{CBO}$                         | $V_{CB} = 50\text{V}, I_E = 0$                             |     |      | 0.1  | $\mu\text{A}$ |
| Emitter cutoff current                  | $I_{EBO}$                         | $V_{EB} = 25\text{V}, I_C = 0$                             |     |      | 0.1  | $\mu\text{A}$ |
| Forward current transfer ratio          | $h_{FE}$                          | $V_{CE} = 2\text{V}, I_C = 4\text{mA}$                     | 500 |      | 2500 |               |
| Forward current transfer $h_{FE}$ ratio | $h_{FE}(\text{small/large})^{*1}$ | $V_{CE} = 2\text{V}, I_C = 4\text{mA}$                     | 0.5 | 0.99 |      |               |
| Collector to emitter saturation voltage | $V_{CE(\text{sat})}$              | $I_C = 30\text{mA}, I_B = 3\text{mA}$                      |     |      | 0.1  | V             |
| Base to emitter voltage                 | $V_{BE}$                          | $V_{CE} = 2\text{V}, I_C = 4\text{mA}$                     |     | 0.6  |      | V             |
| Transition frequency                    | $f_T$                             | $V_{CB} = 6\text{V}, I_E = -4\text{mA}, f = 200\text{MHz}$ |     | 80   |      | MHz           |
| Collector output capacitance            | $C_{ob}$                          | $V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$            |     |      | 7    | pF            |
| ON Resistance                           | $R_{on}^{*2}$                     |  |     | 1.0  |      | $\Omega$      |

\*1 Ratio between 2 elements

\*2  $R_{on}$  test circuit

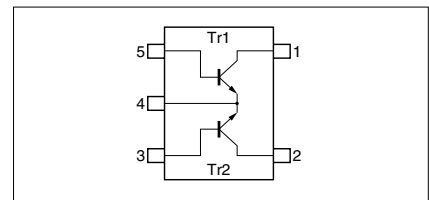


Note) The Part number in the Parenthesis shows conventional part number.

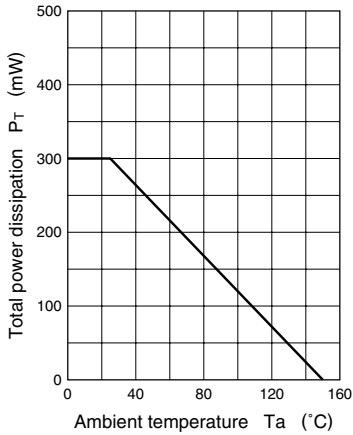


Marking Symbol: 5S

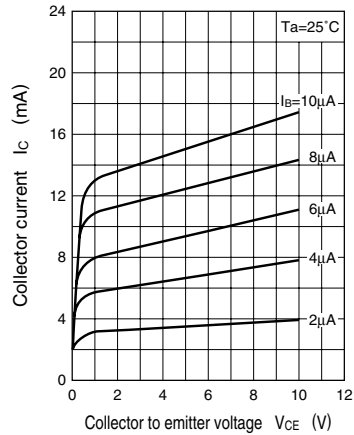
Internal Connection



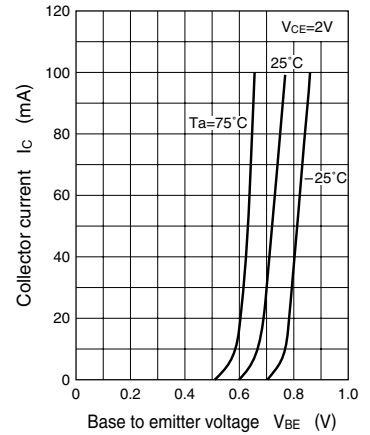
$P_T - T_a$



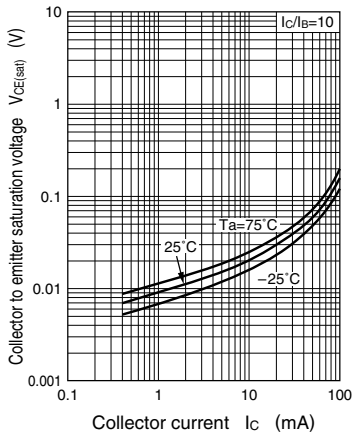
$I_C - V_{CE}$



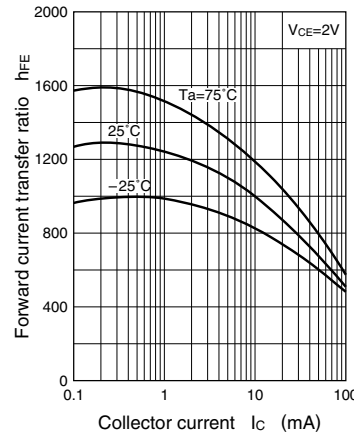
$I_C - V_{BE}$



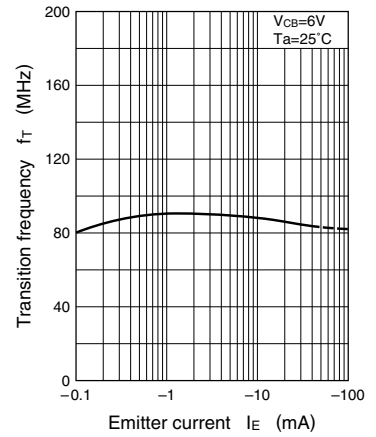
$V_{CE(sat)} - I_C$



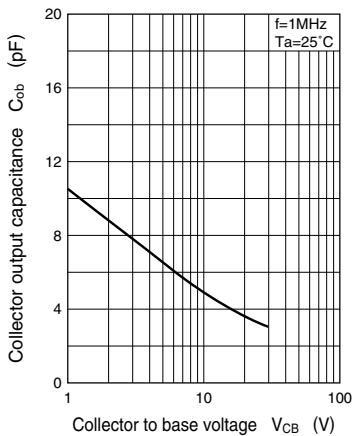
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



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